

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L14	21450	(flatten\$3 or planariz\$3 or smooth\$3) same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:22
L15	600	14 same ((remov\$3 or etch\$3) same (silicon near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:23
L16	129	15 same (expos\$3 same (silicon or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:24
L17	0	16 and ((activat\$3 same gas) same nozzle)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:24
L18	15661	((local\$2 or selective\$2) same etch\$3) same (silicon near oxide or "SiO.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:11
L19	79	L18 same (nozzle same gas\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:35
L20	75	19 and (mov\$3 same nozzle)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:36
L21	35	19 and ((mov\$3 same nozzle) same (substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:36
L22	2085	18 same (mov\$3 same substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:38

L23	0	18 same (mov\$3 same (gas near (injector or ejector or nozzle)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:40
L24	1	18 same (mov\$3 same (injector or ejector or nozzle))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:41
L25	1483	(local\$2 same etch\$3) same (silicon near oxide or "SiO.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 08:58
L26	15	L25 and (spray\$3 same gas\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:03
L27	29	(lateral\$3 near mov\$3) same (gas near (inject\$3 or nozzle))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:04
L28	55	18 and ((relat\$3 near mov\$3) same (substrate or wafer or gas near (inject\$3 or nozzle)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:13
L29	16	28 and @pd<"20020722"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:45
L30	1092	(ion near mill\$3 or charged near particle near beam) same (etch\$3 same silicon or silicon near oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:46
L31	0	30 same (relative near move\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:46
L32	1	30 and (controll\$3 same (relative near move\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:48

L33	0	30 and (control\$3 same ((gas or ion or beam) same (eject\$3 or nozzle) same mov\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:50
L34	0	30 and (control\$3 same (move\$3 near nozzle))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:51
L35	54	30 and (control\$3 same move\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/08 09:51